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# Rod-like Si<sub>3</sub>N<sub>4</sub> grain growth in the sintered body of amorphous Si<sub>3</sub>N<sub>4</sub>-BN composite powder with sintering additives

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The sintered structures of amorphous  $Si_3N_4$ -BN composite powder were investigated with sintering aids from the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> and  $Y_2O_3$ -TiO<sub>2</sub>-AlN systems. In the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> system,  $\beta$ -Si<sub>3</sub>N<sub>4</sub> and h-BN crystallized during sintering. TiN additionally appeared in the  $Y_2O_3$ -TiO<sub>2</sub>-AlN system. The microstructure of the Si<sub>3</sub>N<sub>4</sub>-BN composite was observed by SEM. Flaky BN particles with a length of about 1.0~1.5 µm were observed in the Si<sub>3</sub>N<sub>4</sub> matrix. The Si<sub>3</sub>N<sub>4</sub> matrix had a fine-grained microstructure in the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> system, whereas rod-like Si<sub>3</sub>N<sub>4</sub> grains with a length of 3~10 µm were observed in the  $Y_2O_3$ -TiO<sub>2</sub>-AlN system. The morphology of the TiN particles was observed by TEM. Small TiN particles of about 0.1 µm in diameter were included in large Si<sub>3</sub>N<sub>4</sub> grains, but these fine TiN inclusions were a rare case. Large TiN particles of about 1 µm in diameter were located at grain boundaries throughout the sintered body. The thermal shock resistance of Si<sub>3</sub>N<sub>4</sub> was improved by the BN inclusions in the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> system. With the  $Y_2O_3$ -TiO<sub>2</sub>-AlN system, the TiN inclusions increased the fracture toughness of the Si<sub>3</sub>N<sub>4</sub>-BN composite but the thermal shock resistance was reduced.

Key words: silicon nitride, boron nitride, titanium nitride, composite powder, nanocomposite.

### Introduction

Silicon nitride ceramics are excellent in terms of strength, heat resistance and wear resistance, and their application has been developed as engineering materials for such uses as in gas turbine and engine components, etc. However, their fracture toughness and thermalshock resistance need to be more improved to establish their reliability. Nanocomposites have received a lot of attention as a means of improving their mechanical properties [1]. Hojo *et al.* [2] reported that a  $Si_3N_4$ -BN nanocomposite can be fabricated by the sintering of amorphous Si<sub>3</sub>N<sub>4</sub>-BN composite powder prepared by a vapor phase reaction method. A fine dispersion of h-BN was effective in improving the thermal-shock resistance, but the fracture toughness was reduced due to the inhibition of Si<sub>3</sub>N<sub>4</sub> grain growth by the BN particles. On the other hand, it was found that TiN inclusions accelerate the growth of rod-like Si<sub>3</sub>N<sub>4</sub> grains in a Si<sub>3</sub>N<sub>4</sub>-TiN nanocomposite fabricated from composite powder [3]. Ueno et al. [4] reported that TiN was finely dispersed in a Si<sub>3</sub>N<sub>4</sub> matrix by the in-situ reaction of  $TiO_2$  and AlN included in the sintering aid. Yano *et al.* [5] reported that TiN particles formed in a  $Si_3N_4$  matrix with Y<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN as a sintering aid.

The authors reported that TiN formed in the  $\rm Si_3N_4\text{-}$  BN composite with  $\rm Y_2O_3\text{-}TiO_2\text{-}AlN$  as a sintering aid

and enhanced the rod-like  $Si_3N_4$  grain growth [6], but the mechanism was not clear. In the present paper, to clarify the effect of the inclusion of TiN on the rod-like  $Si_3N_4$  grain growth, the microstructures of  $Si_3N_4$ -BN composites were compared between sintering aids of the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> and  $Y_2O_3$ -TiO<sub>2</sub>-AlN systems, and the mechanical properties (fracture toughness and thermal shock resistance) were measured. The microstructure and properties of monolithic  $Si_3N_4$  were also investigated for comparison.

# **Experimental**

The vapor phase reaction was conducted using a flow-type furnace reactor.  $Si_3N_4$ -BN composite powder was prepared from the SiCl<sub>4</sub>-BCl<sub>3</sub>-NH<sub>3</sub>-H<sub>2</sub> system, and Si<sub>3</sub>N<sub>4</sub> powder from the SiCl<sub>4</sub>-NH<sub>3</sub>-H<sub>2</sub> system. The reaction temperature was 1400°C. The by-product, NH<sub>4</sub>Cl, was removed by sublimation at 400°C in N<sub>2</sub>. The BN content in the composite powder was determined by a chemical analysis. The sintering aids from the Y<sub>2</sub>O<sub>3</sub>(6 wt%)-Al<sub>2</sub>O<sub>3</sub>(2 wt%), Y<sub>2</sub>O<sub>3</sub>(6 wt%)-TiO<sub>2</sub>(2 wt%) and Y<sub>2</sub>O<sub>3</sub>(6 wt%)-TiO<sub>2</sub>(2 wt%) systems were added to the powders by dry milling. Hot pressing was carried out for 2h at 1800°C and 50 MPa in N<sub>2</sub>.

The crystalline phases were identified by X-ray diffraction (XRD). The microstructure was observed by scanning electron microscopy (SEM) and transmission electron microscopy (TEM). The specimens for SEM were polished and plasma-etched with  $CF_4$  containing  $8\%O_2$ . The thin specimens for TEM were prepared by

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polishing, dimple-grinding and final Ar ion-milling. Energy-dispersive X-ray microanalysis (EDX) was also carried out in the TEM observations. The fracture toughness was measured by the Vickers indentation technique (load: 10 kg) and calculated using Niiharaís equation [7]. The thermal shock resistance was evaluated by a quenching method using water at room temperature, in which cracks on the specimen surface were observed with an optical microscope. The test was repeated for each sample with increasing temperature at about 25°C intervals.

# **Results and Discussion**

# Crystalline phases of monolithic $Si_3N_4$ and $Si_3N_4$ -BN composites

Fine  $Si_3N_4$  powder and  $Si_3N_4$ -BN composite powder were produced by the vapor phase reaction method. Figure 1 shows the SEM image of the  $Si_3N_4$ -BN composite particles. The particles were spherical and about 0.1 µm in size.  $Si_3N_4$  particles had a similar morphology. The powders were all amorphous. Hojo *et al.* [8] reported that the composite powder was not a mixture of  $Si_3N_4$  and BN particles, but  $Si_3N_4$  and BN were mixed on nearly a molecular level in each particle.

Figure 2(A) shows the XRD patterns of monolithic  $Si_3N_4$  sintered with additives from the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub>,  $Y_2O_3$ -TiO<sub>2</sub>-AlN and  $Y_2O_3$ -TiO<sub>2</sub> systems. The amorphous powder crystallized into  $\beta$ -Si<sub>3</sub>N<sub>4</sub> during sintering. A small peak of Si was detected. This may be caused by partial decomposition of amorphous  $Si_3N_4$ . Compared to the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> system, a small peak of TiN additionally appeared in the  $Y_2O_3$ -TiO<sub>2</sub>-AlN and  $Y_2O_3$ -TiO<sub>2</sub>-Signer (6) described that amorphous  $Si_3N_4$  reacted with TiO<sub>2</sub> to form  $Si_2N_2O$  and TiN at 1400°C~1600°C.  $Si_2N_2O$  disappeared at 1800°C. In the  $Y_2O_3$ -TiO<sub>2</sub> system,  $Si_2N_2O$  is thought to decompose to  $Si_3N_4$  and  $SiO_2$ . In the  $Y_2O_3$ -TiO<sub>2</sub>-AlN system,  $Si_2N_2O$  can react with AlN to form  $Si_3N_4$  and  $Al_2O_3$ .  $SiO_2$  and  $Al_2O_3$  may dissolve into a liquid phase in the sintering



**Fig. 1.** SEM image of Si<sub>3</sub>N<sub>4</sub>-BN composite powder.



**Fig. 2.** XRD patterns of (A) monolithic  $Si_3N_4$  and (B)  $Si_3N_4$ -BN composites sintered with additives from the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub>,  $Y_2O_3$ -TiO<sub>2</sub>-AlN and  $Y_2O_3$ -TiO<sub>2</sub> systems.

aid.

Figure 2(B) shows the XRD patterns of the  $Si_3N_4$ -BN composite sintered with additives from the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> and  $Y_2O_3$ -TiO<sub>2</sub>-AlN systems.  $\beta$ -Si<sub>3</sub>N<sub>4</sub> and h-BN crystallized and a small amount of silicon formed in both systems. In the case of  $Y_2O_3$ -TiO<sub>2</sub>-AlN system, small peaks of TiN and TiB<sub>2</sub> were detected. The formation of TiN may occur by the same mechanism as in mono-lithic Si<sub>3</sub>N<sub>4</sub>. The formation of TiB<sub>2</sub> results from the reaction between TiO<sub>2</sub> or TiN with BN.

#### Microstructure of the sintered body

Figure 3 shows the SEM images of the etched surface of monolithic Si<sub>3</sub>N<sub>4</sub> sintered with additives from the Y<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub>, Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN and Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub> systems. In the case of the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> system, the sintered body had a fine-grained microstructure, including small needle-like grains. In the case of the Y2O3-TiO2-AlN system, rod-like Si<sub>3</sub>N<sub>4</sub> grains with a length of  $3 \sim 10 \,\mu m$ grew throughout the sintered body. On the other hand, in the  $Y_2O_3$ -TiO<sub>2</sub> system, rod-like Si<sub>3</sub>N<sub>4</sub> grains with a length of about 10  $\mu$ m were observed in a fine Si<sub>3</sub>N<sub>4</sub> matrix, but the number of rod-like grains was less than in the Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN system. These results suggest that rod-like Si<sub>3</sub>N<sub>4</sub> grain growth was stimulated by the TiO<sub>2</sub> addition and that the Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN system was more effective than the Y2O3-TiO2 system. There are two possible reasons for rod-like Si<sub>3</sub>N<sub>4</sub> grain growth in these systems. One is that TiN particles act as nuclei for Si<sub>3</sub>N<sub>4</sub> grain growth. It is well known that the densification and grain growth of Si<sub>3</sub>N<sub>4</sub> occur by a liquidphase mechanism. During the dissolution-precipitation process, TiN might behave as a nucleus to initiate the



Fig. 3. SEM images of etched surface of monolithic  $Si_3N_4$  sintered with additives from the (A)  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub>, (B)  $Y_2O_3$ -TiO<sub>2</sub>-AlN and (C)  $Y_2O_3$ -TiO<sub>2</sub> systems.



**Fig. 4.** SEM images of fracture surface and etched surface of Si<sub>3</sub>N<sub>4</sub>-5.4 vol%BN composites sintered with additives from the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> and  $Y_2O_3$ -TiO<sub>2</sub>-AlN systems. (A) fracture surface,  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> (B) etched surface,  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> (C) etched surface,  $Y_2O_3$ -TiO<sub>2</sub>-AlN.

growth of rod-like  $Si_3N_4$  grains. Another possibility is that the composition of the grain boundary phase was changed by the TiO<sub>2</sub> addition.

The fracture surface of the Si<sub>3</sub>N<sub>4</sub>-BN composite was observed by SEM (Figure 4(A)). Flaky BN particles with a length of about 1.0~1.5  $\mu$ m were observed in the Si<sub>3</sub>N<sub>4</sub> matrix with the use of the Y<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub> and Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN systems [6]. Figure 4(B) shows the SEM image of an etched surface of a Si<sub>3</sub>N<sub>4</sub>-BN composite in the Y<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub> system. The growth of needle-like Si<sub>3</sub>N<sub>4</sub> grains was more noticeable compared to monolithic Si<sub>3</sub>N<sub>4</sub>, but the grain size was small. On the other hand, in the Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN system, rod-like Si<sub>3</sub>N<sub>4</sub> grains with a length of 3~10  $\mu$ m were observed as well as in monolithic Si<sub>3</sub>N<sub>4</sub>. These results indicate that the growth of rod-like Si<sub>3</sub>N<sub>4</sub> grains was also stimulated by the TiO<sub>2</sub> addition in the Si<sub>3</sub>N<sub>4</sub>-BN system.

# Morphology of the TiN particles

The morphology of TiN particles was observed by TEM. Figure 5 shows a TEM image of monolithic Si<sub>3</sub>N<sub>4</sub> sintered with additives from the Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN system. Large and small particles with darker contrast were observed as shown by an arrow. Small particles with a size of 0.1  $\mu$ m were included within large Si<sub>3</sub>N<sub>4</sub> grains, and large particles with a size of 1 µm were located at the grain boundaries. By EDX analysis, Ti and N were detected in these particles, indicating that these particles were TiN. Large TiN particles were observed throughout the sintered body, but the fine TiN inclusions were a rare case. It is difficult to postulate that the TiN particles act as nuclei because the TiN particles were rarely observed in Si<sub>3</sub>N<sub>4</sub> grains. Therefore, the rod-like Si<sub>3</sub>N<sub>4</sub> grain growth may be related to a change in liquid phase composition at the grain boundaries by the  $TiO_2$  addition.



Fig. 5. TEM image of monolithic  $Si_3N_4$  sintered with additives from the  $Y_2O_3$ -TiO<sub>2</sub>-AlN system.

#### Fracture toughness and thermal shock resistance

The mechanical properties of monolithic Si<sub>3</sub>N<sub>4</sub> and Si<sub>3</sub>N<sub>4</sub>-BN composite are summarized in Table 1. In monolithic  $Si_3N_4$  sintered with the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> sintering aid, the fracture toughness was  $6.3 \text{ MPa} \cdot \text{m}^{1/2}$  and the thermal-shock resistance was 700°C. It has been reported that the addition of h-BN particles to Si<sub>3</sub>N<sub>4</sub> is effective in improving the thermal-shock resistance because the thermal stress can be absorbed by the low elastic modulus h-BN [8]. In the present work with Y<sub>2</sub>O<sub>3</sub>- $Al_2O_3$  as a sintering aid, the thermal-shock resistance of the Si<sub>3</sub>N<sub>4</sub>-BN composite increased to 770°C, but the fracture toughness decreased to 5.5 MPa·m<sup>1/2</sup>. On the other hand, with the Y<sub>2</sub>O<sub>3</sub>-TiO<sub>2</sub>-AlN sintering aid, the fracture toughness increased to 6.6 MPa·m<sup>1/2</sup>, but the thermal-shock resistance decreased to 700°C. The improvement of fracture toughness may be due to crack deflection by rod-like Si<sub>3</sub>N<sub>4</sub> grains. The decrease in thermal shock resistance may be caused by large TiN inclusions because TiN has a large thermal expansion coefficient. A fine dispersion of TiN is required to achieve excellent mechanical properties.

#### Conclusions

Fine  $Si_3N_4$ -BN composite powder was prepared by a vapor phase reaction method. When  $Y_2O_3$ -TiO<sub>2</sub>-AlN was used as sintering aid, TiN formed in addition to  $\beta$ -

Table 1. Mechanical properties of monolithic  $\mathrm{Si}_3\mathrm{N}_4$  and  $\mathrm{Si}_3\mathrm{N}_4\text{-}\mathrm{BN}$  composites

Sample	Sintering aid	BN (vol%)	Properties of sintered body		
			dr (%)	K <sub>IC</sub> (MPa·m <sup>1/2</sup> )	ΔT (°C)
Si <sub>3</sub> N <sub>4</sub>	$\begin{array}{c} 6 \text{ wt\% } Y_2 O^3 \text{-} \\ 2 \text{ wt\% } Al^2 O_3 \end{array}$	0	97.4	6.3	700
Si <sub>3</sub> N <sub>4</sub> -BN	$\begin{array}{c} 6 \text{ wt\% } Y_2O_3\text{-} \\ 2 \text{ wt\% } Al_2O_3 \end{array}$	5.4	96.1	5.5	775
	6 wt% Y <sub>2</sub> O <sup>3</sup> - 2 wt% TiO <sub>2</sub> - 1.6 wt% AlN	5.4	96.7	6.6	700

dr: relative density. K<sub>IC</sub>: fracture toughness.

 $\Delta T$ : critical temperature difference for crack initiation.

 $Si_3N_4$  and h-BN. The addition of  $TiO_2$  and AlN to the  $Y_2O_3$  sintering aid enhanced the rod-like grain growth even in the  $Si_3N_4$ -BN composite. The rod-like  $Si_3N_4$  grain growth may be related to a liquid composition change in the grain boundary phase. The thermal shock resistance of  $Si_3N_4$  was improved by the BN inclusions in the  $Y_2O_3$ -Al<sub>2</sub>O<sub>3</sub> system. With the  $Y_2O_3$ -TiO<sub>2</sub>-AlN system, the TiN inclusions increased the fracture toughness of the  $Si_3N_4$ -BN composite but decreased the thermal shock resistance.

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